

ABSTRACT

A light-receiving element array is provided in which the degradation of characteristic thereof due to the crosstalk may be prevented. An n-InP layer, an i-InGaAs layer, and an
5 n-InP layer are stacked on an n-InP substrate. Zn is diffused into the topmost n-InP layer to form a p-type diffused region, resulting in a pin-photodiode. A passivation layer is deposited on the structure to a thickness such that a nonreflective condition is satisfied.
10 On the passivation film, a light-shielding film is provided so as to cover the area between light-receiving elements.